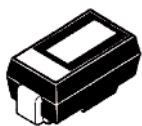


Schottky Rectifier, 1.0 A



SMB



FEATURES

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level



RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{F(AV)}$	1.0 A
V_R	60 V

DESCRIPTION

The VS-10BQ060PbF surface mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Rectangular waveform	1.0	A
V_{RRM}		60	V
I_{FSM}	$t_p = 5 \mu s$ sine	700	A
V_F	1.0 Apk, $T_J = 125^\circ C$	0.57	V
T_J	Range	- 55 to 150	$^\circ C$

VOLTAGE RATINGS

PARAMETER	SYMBOL	VS-10BQ060PbF	UNITS
Maximum DC reverse voltage	V_R	60	V
Maximum working peak reverse voltage	V_{RWM}		

ABSOLUTE MAXIMUM RATINGS

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current	I _{F(AV)}	50 % duty cycle at T _L = 103 °C, rectangular waveform		1.0	A
Maximum peak one cycle non-repetitive surge current	I _{FSM}	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated V _{RRM} applied	700	A
		10 ms sine or 6 ms rect. pulse		42	
Non-repetitive avalanche energy	E _{AS}	T _J = 25 °C, I _{AS} = 1 A, L = 4 mH		2.0	mJ
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero in 1 μs Frequency limited by T _J maximum V _A = 1.5 x V _R typical		1.0	A

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop See fig. 1	V _{FM} ⁽¹⁾	1 A	T _J = 25 °C	0.6	V
		2 A		0.76	
		1 A	T _J = 125 °C	0.57	
		2 A		0.69	
Maximum reverse leakage current See fig. 2	I _{RM} ⁽¹⁾	T _J = 25 °C	V _R = Rated V _R	0.1	mA
		T _J = 125 °C		5.0	
Typical junction capacitance	C _T	V _R = 5 V _{DC} (test signal range 100 kHz to 1 MHz), 25 °C		62	pF
Typical series inductance	L _S	Measured lead to lead 5 mm from package body		2.0	nH
Maximum voltage rate of charge	dV/dt	Rated V _R		10 000	V/μs

Note

⁽¹⁾ Pulse width < 300 μ s, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	$T_J^{(1)}, T_{Stg}$		- 55 to 150	°C
Maximum thermal resistance, junction to lead	$R_{thJL}^{(2)}$	DC operation	36	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		80	
Approximate weight			0.10	g
			0.003	oz.
Marking device		Case style SMB (similar DO-214AA)	V1H	

Notes

⁽¹⁾ $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink

⁽²⁾ Mounted 1" square PCB

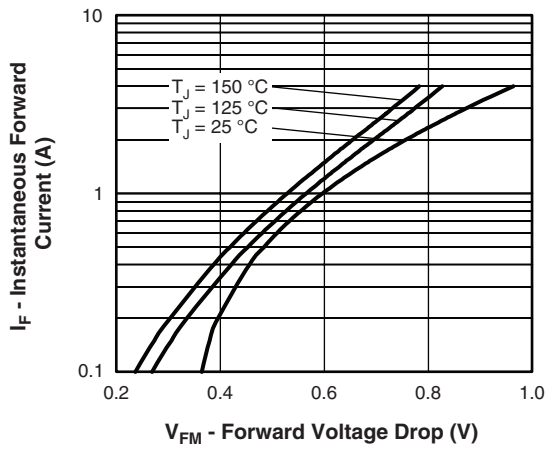


Fig. 1 - Maximum Forward Voltage Drop Characteristics

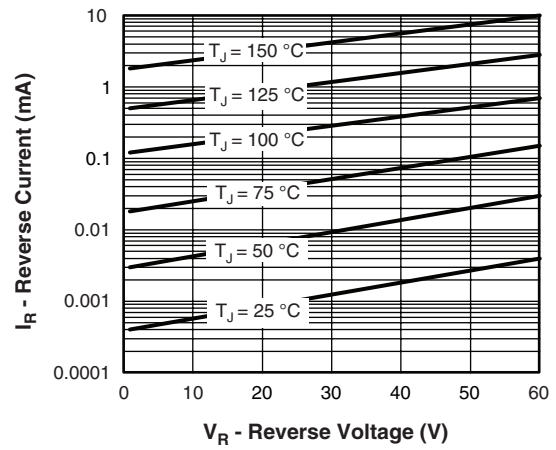


Fig. 2 - Typical Peak Reverse Current vs. Reverse Voltage

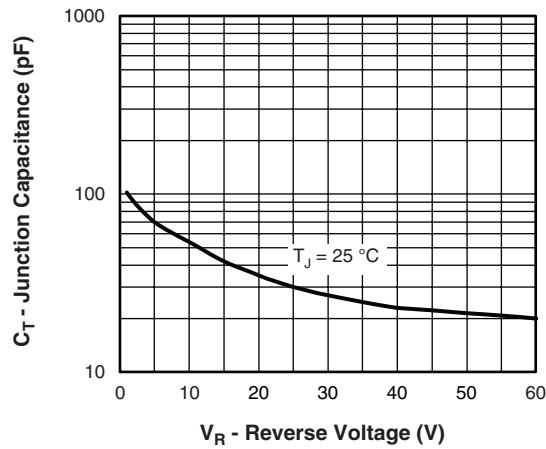


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

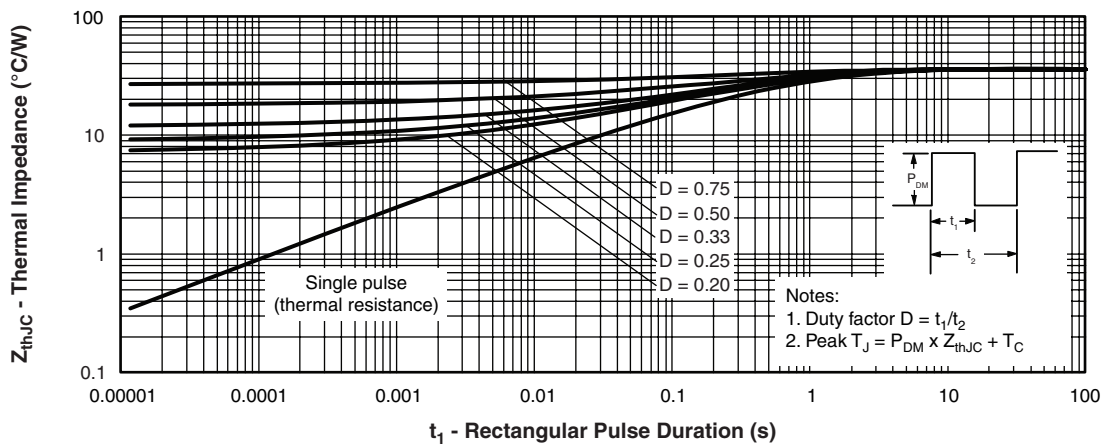


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

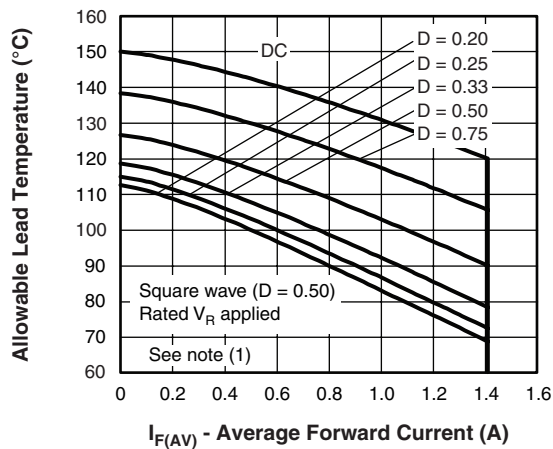


Fig. 5 - Maximum Average Forward Current vs. Allowable Lead Temperature

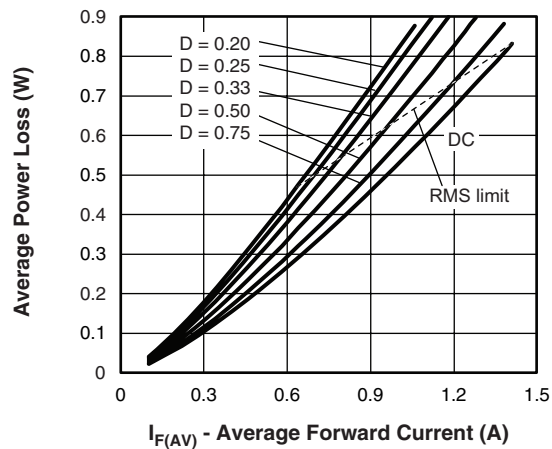


Fig. 6 - Maximum Average Forward Dissipation vs. Average Forward Current

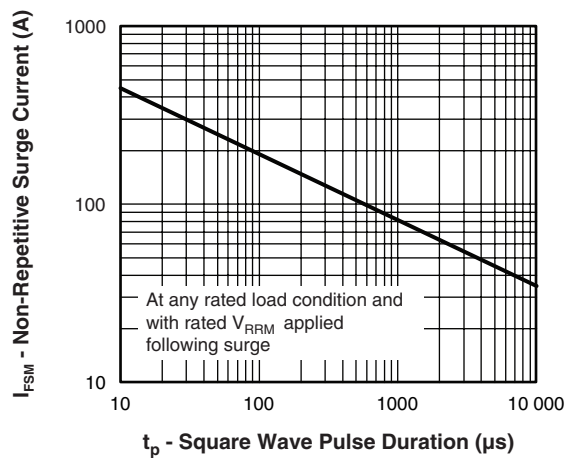


Fig. 7 - Maximum Peak Surge Forward Current vs. Pulse Duration

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 $P_{d_{REV}}$ = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80\%$ rated V_R